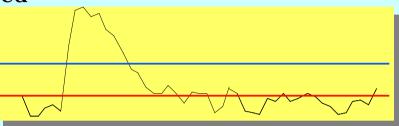
### Noise

### •What is NOISE? <u>A</u> definition:

Any unwanted signal obscuring signal to be observed

two main origins



#### •EXTRINSIC NOISE examples...

pickup from external sources unwanted feedback
 RF interference from system or elsewhere, power supply fluctuations
ground currents
 small voltage differences => currents can couple into system

may be hard to distinguish from genuine signalsbutAVOIDABLEAssembly & connections, especially to ground, are important

#### •INTRINSIC NOISE

Fundamental property of detector or amplifying electronics Can't be eliminated but can be MINIMISED

1

# Origins of noise in amplifying systems

#### •1. Thermal noise

Quantum-statistical phenomenon

Charge carriers in constant thermal motion macroscopic fluctuations in electrical state of system

### •2. Shot noise

Random fluctuations in DC current flow originates in quantisation of charge non-continuous current

### •3. 1/f noise

Characteristic of many physical systems least well understood noise source *commonly associated with interface states in MOS electronics* 

### **Thermal noise (i)**

•Einstein (1906), Johnson, Nyquist (1928) e.g. resistor:  $\sim 10^{23}$  possible states macroscopic statistical average over micro-states •Experimental observation Mean voltage <v> = 0 $\langle v^2 \rangle = 4kT.R.$  f f = observing bandwidth Variance  $(v) = \langle v^2 \rangle = 1.3 \ 10^{-10} \ (R. \ f)^{1/2}$  volts at 300K gaussian distribution of fluctuations in v e.g. R = 1M f = 1Hz  $(v) = 0.13\mu V$ Noise power = 4kT. f independent of R & q independent of f - WHITE •Quantum effects Normal mode energies:  $kT = hf/(e^{hf/kT} - 1)$   $kT \gg hf$ 

at  $300^{\circ}$ K kT = 0.026 eV hf = kT at f = 6.10<sup>12</sup> Hz

# **Thermal noise (ii)**



Noise generator + noiseless resistance R

### •Spectral densities

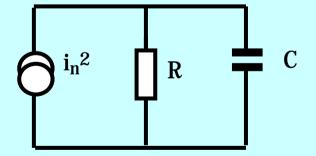
mean square noise voltage or current per unit frequency interval

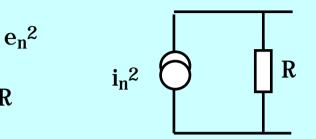
 $w_V(f) = 4kTR$  (voltage)  $w_I(f) = 4kT/R$  (current)

### •Why not infinite fluctuation in infinite bandwidth?

- A-1: QM formula -> 0 at high f
- A-2: real components have capacitive behaviour (high f)
- or inductive (low f).

with R and C in parallel  $\langle v^2 \rangle = kT/C$ 

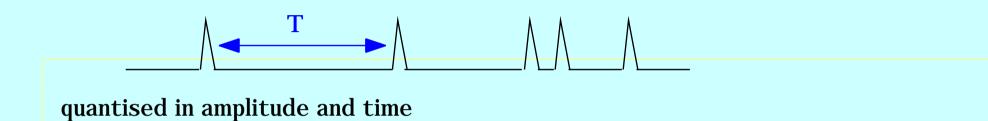




### Shot noise

#### •Poisson fluctuations of charge carrier number

eg arrival of charges at electrode in system - induce charges on electrode



•Examples

electrons/holes crossing potential barrier in diode or transistor electron flow in vacuum tube

$$\langle i_n^2 \rangle = 2qI.$$
 f WHITE

(NB notation e = q)

# I = DC current

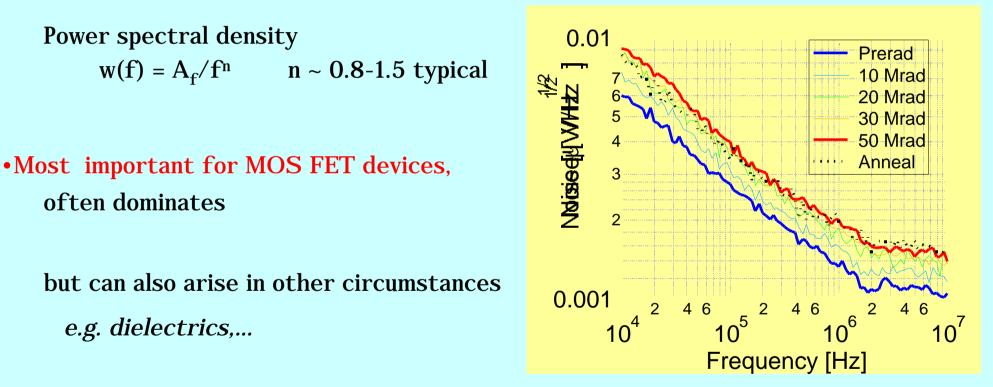
#### gaussian distribution of fluctuations in i

5

### 1/f noise

•White noise sources frequently dominate in many real systems however frequency dependent noise is also common

•1/f noise is a generic term for a wide range of phenomena, possibly not always related



pMOS transistor noise spectrum

# An explanation for 1/f noise

Silicon MOS transistors are very sensitive to oxide interface typically populated by band-gap energy levels (traps) traps exchange charge with channel - ie. emit and capture electrons or holes
Traps have lifetime to retain charge h(t) ~ e<sup>-t/</sup> Expect a range of traps with different time constants, distributed with p() in frequency domain H() ~ 1/(1+j)

Deduce frequency spectrum by integrating over all values of

 $w(f) \sim (0, p(t))|H(t)|^2 d$ 

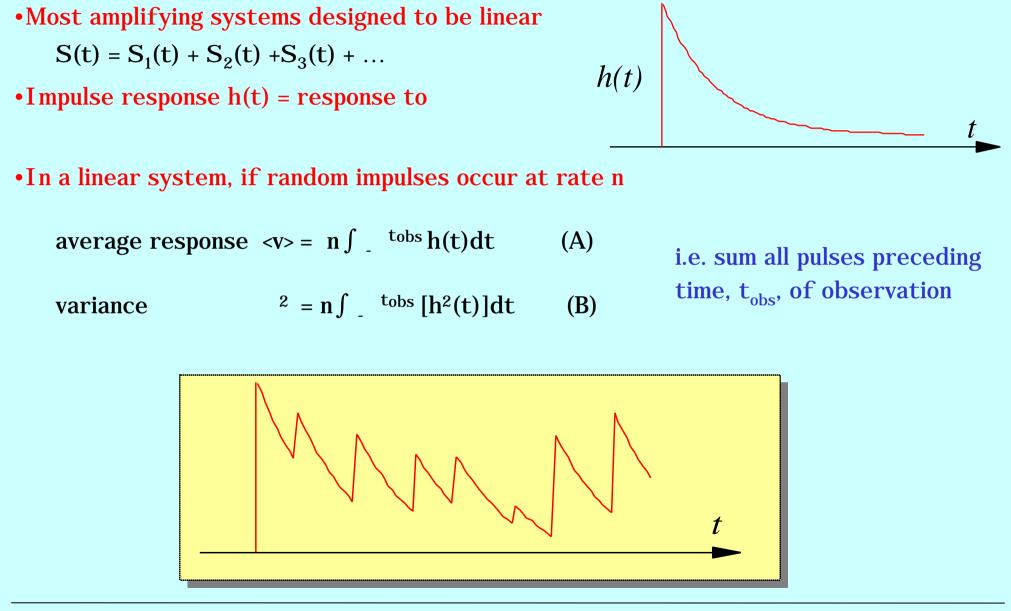
If p() = constant, ie all time constants equally probable

w(f) ~  $_0$  d /(1 +  $^2$   $^2$ ) [standard integral, put tan = ] = A/f

Many other real-life processes have  $e^{-t/}$  time distributions -

typical of random, Poisson-type processes

### **Campbell's theorem - time domain**



# **Campbell's theorem - frequency domain**

•Recall relationship between impulse response h(t) and transfer function H() H() =  $\int_{-}^{-} h(t) e^{-j t} dt$  h(t) =  $\int_{-}^{-} H() e^{-j t} df$  H() =  $v_{out}() / v_{in}()$ 

•Rewrite (B) using Parseval's Theorem

$$\int_{-} h^{2}(t) dt = |H()|^{2} df = 2 \int_{0} |H()|^{2} df$$

h(t) is real and thus H(- ) = H<sup>\*</sup>( )

**so**  $^{2} = n \int_{-}^{-} h^{2}(t) dt = n \int_{-}^{-} |H()|^{2} df$ 

This relates noise spectral densities at input and output:

 $w_{out}(f) = w_{in}(f) |H()|^2$  can use theorem to calculate system response to noise

•eg. shot noise Consider impulse response to be impulse (ie unchanged!)

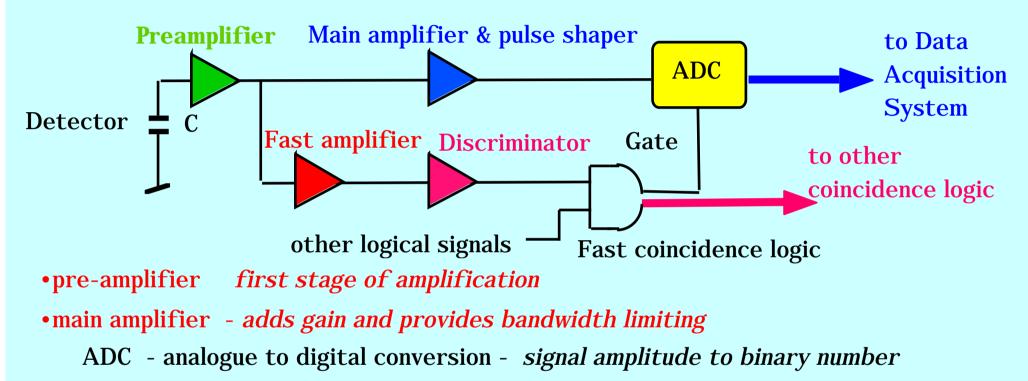
$$h(t) = e(t) \implies H() = 1.e$$

$$^{2} = n e^{2} \int_{-\infty}^{-\infty} (t) dt = ne^{2} \int_{-\infty}^{-\infty} |H(t)|^{2} dt = 2ne^{2} f$$

but 
$$n = I/e \implies 2 = 2eI f$$

# **Amplifier systems for spectroscopy**

•typical application - precise measurements of x-ray or gamma-ray energies



• fast amplifier and logic -

start ADC ("gate") and flag interesting "events" to DAQ system

- most signals arrive randomly in time.

Other logic required to maximise chance of "good" event, eg second detector